L Number	Hits	Search Text	DB	Time stamp
_	4	'gate oxide' and 'in-situ steam generation'	USPAT; US-PGPUB; EPO; JPO;	2003/08/22 07:29
_	7	@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/08/22 07:29
-	1	@ad<=20020219 and 'ONO' and 'ISSG'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 08:28
-	10	@ad<=20020219 and 'in-situ steam generation' or 'ISSG'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/24 08:32
-	52	(438/954).CCLS.	IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/24 13:24
-	245	(438/593).ccls. and @ad<=20020119	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	627	(438/770).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	481	(438/264).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	208	(438/594).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:27
-	518	(438/275).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	323	(438/199).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24
-	91	(438/477).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:28
-	77	(438/216).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/05/24 13:28
-	577	(438/287).ccls. and @ad<=20020119	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/05/24 13:29
L			IBM TDB	

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7	_

T-	166	(438/783).ccls. and @ad<=20020119	USPAT;	2002/05/24
	100	(450/705).ccis. and ead(-20020119	US-PGPUB;	13:29
			EPO; JPO;	13.23
			DERWENT;	
			IBM TDB	
_	8	'gate oxide' and 'in-situ steam	USPAT;	2002/10/16
		generation' or 'LP-RTP'	US-PGPUB;	10:36
		, , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	2	("5324675").PN.	USPAT;	2002/10/16
			US-PGPUB;	10:11
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	'thin film transistor' and 'gate oxide'	USPAT;	2002/10/16
		and 'in-situ steam generation' or	US-PGPUB;	10:49
		'LP-RTP'	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	27216	@ad<=20020219 and 'TFT'	USPAT;	2002/10/16
			US-PGPUB;	10:35
			EPO; JPO;	
			DERWENT;	
1		(A-14-20020210	IBM_TDB	2002/12/16
_	0	(@ad<=20020219 and 'TFT') and 'oxide' and	USPAT;	2002/10/16
		'ISSG'	US-PGPUB;	10:38
			EPO; JPO; DERWENT;	
			IBM TDB	
l _	0	(@ad<=20020219 and 'TFT') and 'oxide' and	USPAT;	2002/10/16
	"	'in-situ steam generation'	US-PGPUB;	10:38
		in situ steam generation	EPO; JPO;	10.50
			DERWENT;	
			IBM TDB	
_	0	(@ad<=20020219 and 'TFT') and 'oxide' and	USPAT;	2002/10/16
		'LP-RTP'	US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	226	(@ad<=20020219 and 'TFT') and 'floating	USPAT;	2002/10/16
		gate'	US-PGPUB;	10:39
			EPO; JPO;	
			DERWENT;	
1_	1.00	(And/-20020210 and Impm!) and lawida!	IBM_TDB	2002/10/16
1	109	(@ad<=20020219 and 'TFT') and 'oxide' and	USPAT; US-PGPUB;	10:55
		'floating gate'	EPO; JPO;	10.55
			DERWENT;	
			IBM TDB	
_	1	'tft' and 'in-situ steam generation' or	USPAT;	2002/10/16
	•	'LP-RTP'	US-PGPUB;	11:12
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	0	'tft' and 'in-situ steam generation'	USPĀT;	2002/10/16
			US-PGPUB;	10:51
			EPO; JPO;	
1			DERWENT;	
1]	(0.1, 0.0000000) 1.5	IBM_TDB	0000/10/5
-	64	(@ad<=20020219 and 'TFT') and 'oxide	USPAT;	2002/10/16
1		layer' and 'floating gate'	US-PGPUB;	11:04
1			EPO; JPO;	
i			DERWENT; IBM TDB	
_	571	(438/149).CCLS.	USPAT;	2002/10/16
1	"	(.55, 115), 6516.	US-PGPUB;	11:05
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	•			·

	1 1 1 1 1	10-14 0000014 1 /400/11/01		1 2 2 2 1 2 1 2 2 2 2 2 2 2 2 2 2 2 2 2
-	11	<pre>@ad<=20020214 and (438/149).ccls. and 'floating gate'</pre>	USPAT;	2002/10/16
1		i iioaciny gace	US-PGPUB; EPO; JPO;	11:06
			DERWENT;	
			IBM_TDB	
-	3585		USPAT;	2002/10/17
		or (438/770) or (438/264) or (438/275) or		09:50
		(438/199) or (438/477) or (438/216) or (438/287) or (438/783)).CCLS.	EPO; JPO;	
		(436/267) OF (436/763)).CCLS.	DERWENT; IBM TDB	
_	15	@ad<=20020219 and 'ISSG'	USPAT;	2003/02/26
			US-PGPUB;	11:57
			EPO; JPO;	
	:		DERWENT;	
_] ,,	0.d<-20020210 and 10V01 and 14 air.	IBM_TDB	2002/00/06
-	29	<pre>@ad<=20020219 and 'ONO' and 'in-situ steam generation' or 'ISSG'</pre>	USPAT; US-PGPUB;	2003/02/26
		Steam generation of 1556	EPO; JPO;	12.54
			DERWENT;	
			IBM TDB	
-	27	@ad<=20020219 and 'ISSG'	USPAT;	2003/02/26
			US-PGPUB;	12:07
			EPO; JPO; DERWENT;	
			IBM TDB	
-	2	@ad<=20020219 and 'low pressure rapid	USPAT;	2003/02/26
	[thermal process'	US-PGPUB;	12:17
			EPO; JPO;	
			DERWENT;	
_	416	@ad<=20020219 and 'TFT' and 'ONO'	IBM_TDB	2003/02/27
	410	Gadv-20020219 and TFT and ONO.	USPAT; US-PGPUB;	2003/02/27 07:12
			EPO; JPO;	5,.12
			DERWENT;	
			IBM_TDB	
-	0	@ad<=20020219 and 'TFT' and 'ONO' and	USPAT;	2003/02/27
		'ISSG'	US-PGPUB;	07:12
]			EPO; JPO; DERWENT;	
1			IBM TDB	
-	0	@ad<=20020219 and 'TFT' and 'ISSG'	USPĀT;	2003/02/27
			US-PGPUB;	07:13
			EPO; JPO;	
			DERWENT; IBM TDB	
] -	71	@ad<=20020219 and 'in-situ steam	USPAT;	2003/08/22
		generation' or 'ISSG'	US-PGPUB;	08:16
			EPO; JPO;	
			DERWENT;	
_	2	("6525384").PN.	<pre>IBM_TDB USPAT;</pre>	2003/08/22
		\ \\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	USPAT; US-PGPUB;	09:48
			EPO; JPO;	55.40
			DERWENT;	
			IBM_TDB	
⁻	2	"20030155582"	USPAT;	2004/02/23
]			US-PGPUB; EPO; JPO;	09:45
			DERWENT;	
			IBM_TDB	
-	2	'TFT' and 'in-situ steam generation'	USPĀT;	2004/02/23
			US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT; IBM TDB	
-	2	("5700699").PN.	USPAT;	2004/02/23
		·	US-PGPUB;	09:59
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	

-	0	'thin film transistor' near 'issg'	USPAT;	2004/02/23
		1	US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT;	
,			IBM TDB	
-	0	'tft' near 'issg'	USPAT;	2004/02/23
		•	US-PGPUB;	10:04
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	'TFT' near 'in-situ steam generation'	USPAT;	2004/02/23
1		_	US-PGPUB;	10:30
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	0	'TFT' near 'free radical enhanced rapid	USPĀT;	2004/02/23
		thermal oxidation'	US-PGPUB;	10:31
			EPO; JPO;	
			DERWENT;	ł
			IBM TDB	
-	0	'TFT' same 'free radical enhanced rapid	USPAT;	2004/02/23
		thermal oxidation'	US-PGPUB;	10:32
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	1	'TFT' and 'free radical enhanced rapid	USPAT;	2004/02/23
		thermal oxidation'	US-PGPUB;	10:32
			EPO; JPO;	
			DERWENT;	
			IBM TDB	1